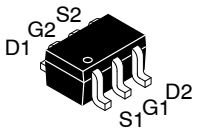
Digital FET, Dual N & P Channel

FDG6321C



SC−88/SC70−6/SOT−363
CASE 419B−02

General Description

These dual N & P−Channel logic level enhancement mode field effect transistors are produced using **onsemi**'s proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on−state resistance. This device has been designed especially on low voltage replacement for bipolar digital transistors and small signal MOSFETS. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.

Features

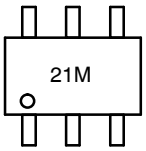
- N−Ch 0.50 A, 25 V
  - $R_{DS(ON)}$ = 0.45 Ω @ V_{GS} = 4.5 V
  - $R_{DS(ON)}$ = 0.60 Ω @ V_{GS} = 2.7 V
- P−Ch −0.41 A, −25 V
  - $R_{DS(ON)}$ = 1.1 Ω @ V_{GS} = −4.5 V
  - $R_{DS(ON)}$ = 1.5 Ω @ V_{GS} = −2.7 V
- Very Small Package Outline SC70−6
- Very Low Level Gate Drive Requirements Allowing Direct Operation in 3 V Circuits ($V_{GS(th)}$ < 1.5 V)
- Gate−Source Zener for ESD Ruggedness (>6 kV Human Body Model)
- These Devices are Pb−Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter		N−Channel	P−Channel	Units
V_{DSS}	Drain−Source Voltage		25	−25	V
V_{GSS}	Gate−Source Voltage		8	−8	V
I_D	Drain Current	Continuous	0.5	−0.41	A
		Pulsed	1.5	−1.2	
P_D	Maximum Power Dissipation (Note 1)		0.3		W
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to 150		°C
ESD	Electrostatic Discharge Rating MIL−STD−883D Human Body Model (100 pF / 1500 Ω)		6		kV

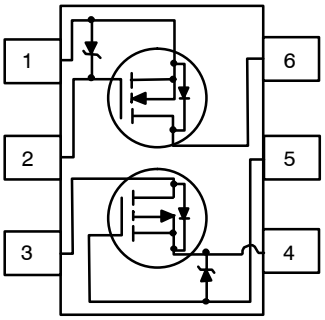
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MARKING DIAGRAM



21 = Specific Device Code
M = Assembly Operation Month

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping†
FDG6321C	SC−88/SC70−6/ SOT−363 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1)	415	°C/W

1. $R_{\theta JA}$ is the sum of the junction−to−case and case−to−ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ = 415°C/W on minimum pad mounting on FR−4 board in still air.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	N−Ch	25	–	–	V
		V_{GS} = 0 V, I_D = −250 μA	P−Ch	−25	–	–	
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	N−Ch	–	26	–	mV/°C
		I_D = −250 μA, Referenced to 25°C	P−Ch	–	−22	–	
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V	N−Ch	–	–	1	μA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55°C		–	–	10	
I_{GSS}	Gate−Body Leakage Current	V_{DS} = −20 V, V_{GS} = 0 V	P−Ch	–	–	−1	μA
		V_{DS} = −20 V, V_{GS} = 0 V, T_J = 55°C		–	–	−10	
I_{GSS}	Gate−Body Leakage Current	V_{GS} = 8 V, V_{DS} = 0 V	N−Ch	–	–	100	nA
		V_{GS} = −8 V, V_{DS} = 0 V	P−Ch	–	–	−100	
ON CHARACTERISTICS (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	N−Ch	0.65	0.8	1.5	V
		V_{DS} = V_{GS}, I_D = −250 μA	P−Ch	−0.65	−0.82	−1.5	
$\Delta V_{GS(th)}$ / ΔT_J	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	N−Ch	–	−2.6	–	mV/°C
		I_D = −250 μA, Referenced to 25°C	P−Ch	–	2.1	–	
$R_{DS(ON)}$	Static Drain−Source On−Resistance	V_{GS} = 4.5 V, I_D = 0.5 A	N−Ch	–	0.34	0.45	Ω
		V_{GS} = 4.5 V, I_D = 0.5 A, T_J = 125°C		–	0.55	0.72	
		V_{GS} = 2.7 V, I_D = 0.2 A		–	0.44	0.6	
		V_{GS} = −4.5 V, I_D = −0.41 A	P−Ch	–	0.85	1.1	
		V_{GS} = −4.5 V, I_D = −0.41 A, T_J = 125°C		–	1.2	1.8	
		V_{GS} = −2.7 V, I_D = −0.05 A		–	1.15	1.5	
$I_{D(ON)}$	On−State Drain Current	V_{GS} = 4.5 V, V_{DS} = 5 V	N−Ch	0.5	–	–	A
		V_{GS} = −4.5 V, V_{DS} = −5 V	P−Ch	−0.41	–	–	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 0.5 A	N−Ch	–	1.45	–	S
		V_{DS} = −5 V, I_D = −0.41 A	P−Ch	–	0.9	–	
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	N−Channel V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz P−Channel V_{DS} = −10 V, V_{GS} = 0 V, f = 1.0 MHz	N−Ch	–	50	–	pF
			P−Ch	–	62	–	
C_{oss}	Output Capacitance		N−Ch	–	28	–	
			P−Ch	–	34	–	
C_{rss}	Reverse Transfer Capacitance		N−Ch	–	9	–	
			P−Ch	–	10	–	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (continued)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 2)							
$t_{D(on)}$	Turn-On Delay Time	N−Channel V_{DD} = 5 V, I_D = 0.5 A, V_{GS} = 4.5 V, R_{GEN} = 50 Ω P−Channel V_{DD} = −5 V, I_D = −0.5 A, V_{GS} = −4.5 V, R_{GEN} = 50 Ω	N−Ch	−	3	6	ns
			P−Ch	−	7	15	
t_r	Turn-On Rise Time		N−Ch	−	8.5	18	ns
			P−Ch	−	8	16	
$t_{D(off)}$	Turn-Off Delay Time		N−Ch	−	17	30	ns
			P−Ch	−	55	80	
t_f	Turn-Off Fall Time		N−Ch	−	13	25	ns
			P−Ch	−	35	60	
Q_g	Total Gate Charge	N−Channel V_{DS} = 5 V, I_D = 0.5 A, V_{GS} = 4.5 V P−Channel V_{DS} = −5 V, I_D = −0.41 A, V_{GS} = −4.5 V	N−Ch	−	1.64	2.3	nC
			P−Ch	−	1.1	1.5	
Q_{gs}	Gate−Source Charge		N−Ch	−	0.38	−	nC
			P−Ch	−	0.31	−	
Q_{gd}	Gate−Drain Charge		N−Ch	−	0.45	−	nC
			P−Ch	−	0.29	−	
DRAIN−SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
I_S	Maximum Continuous Drain−Source Diode Forward Current		N−Ch	−	−	0.25	A
			P−Ch	−	−	−0.25	
V_{SD}	Drain−Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.5 A (Note 2)	N−Ch	−	0.8	1.2	V
		V_{GS} = 0 V, I_S = −0.5 A (Note 2)	P−Ch	−	−0.8	−1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

TYPICAL PERFORMANCE CHARACTERISTICS: N−CHANNEL

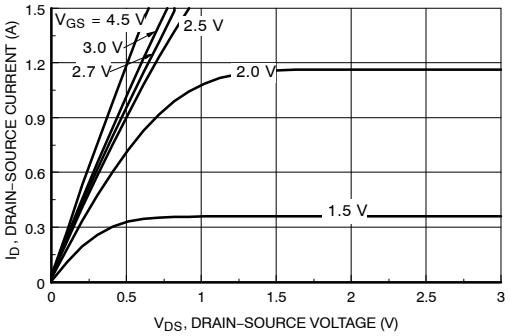


Figure 1. On−Region Characteristics

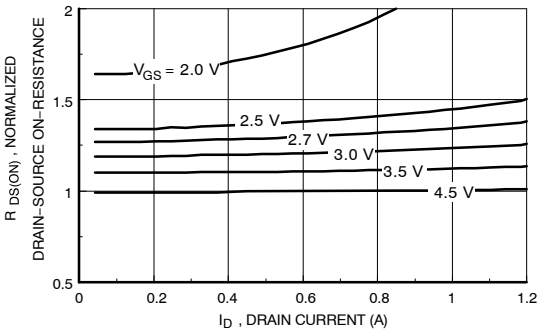


Figure 2. On−Resistance Variation with Drain Current and Gate Voltage

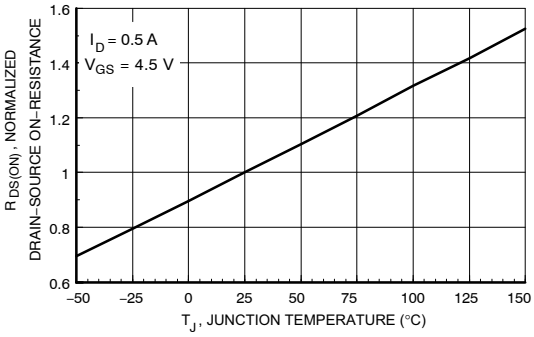


Figure 3. On−Resistance Variation with Temperature

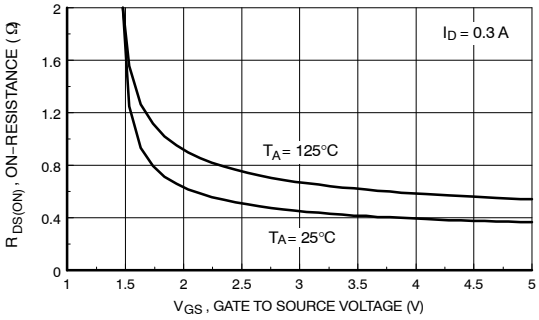


Figure 4. On−Resistance Variation with Gate−to−Source Voltage

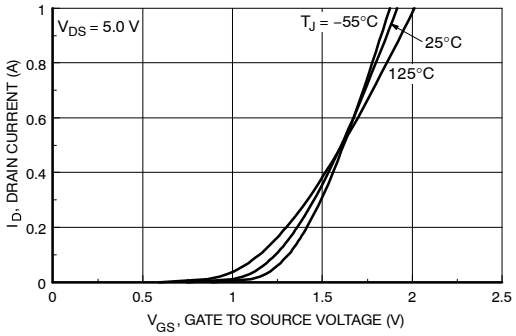


Figure 5. Transfer Characteristics

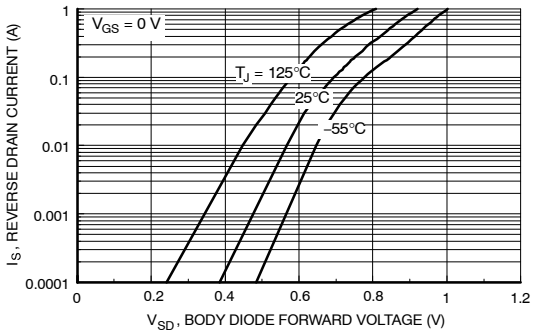


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL PERFORMANCE CHARACTERISTICS: N−CHANNEL (CONTINUED)

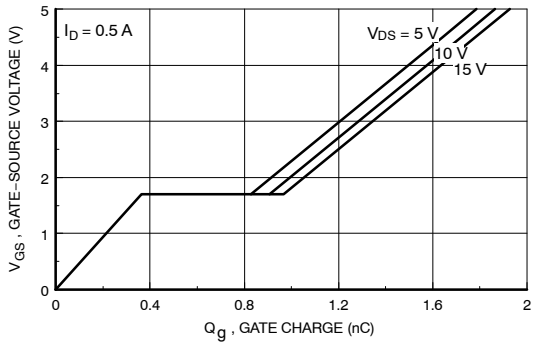


Figure 7. Gate Charge Characteristics

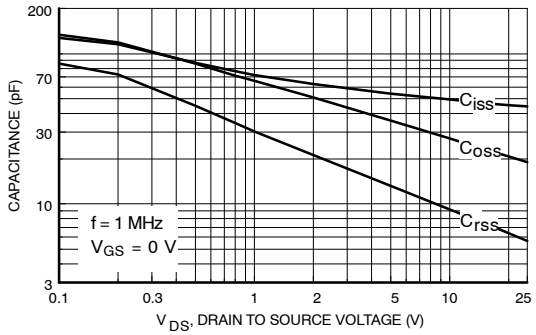


Figure 8. Capacitance Characteristics

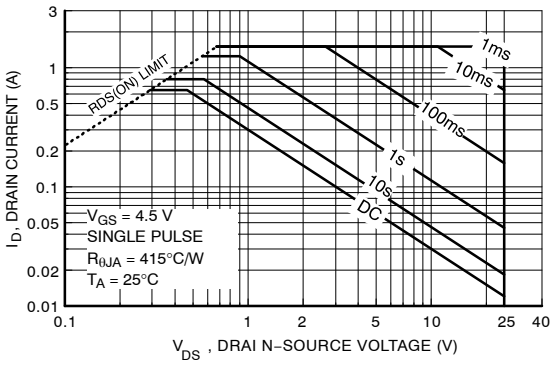


Figure 9. Maximum Safe Operating Area

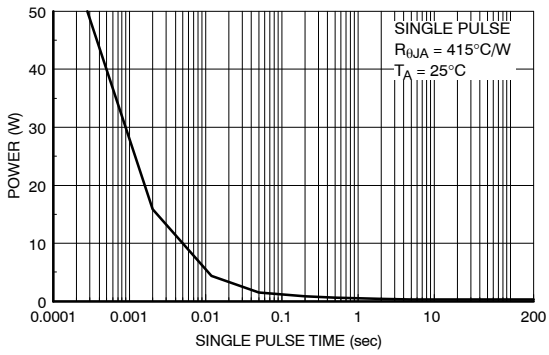


Figure 10. Single Pulse Maximum Power Dissipation

TYPICAL PERFORMANCE CHARACTERISTICS: P−CHANNEL

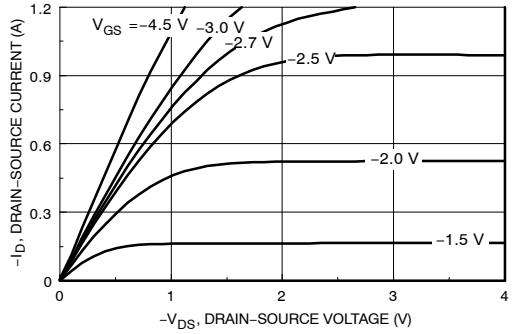


Figure 11. On−Region Characteristics

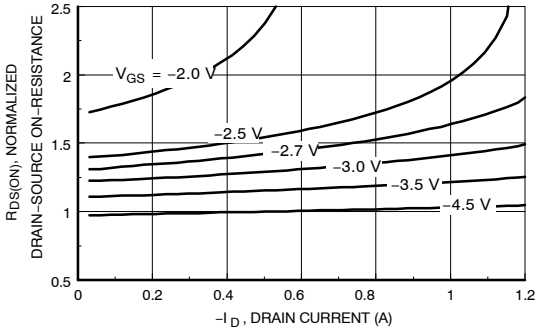


Figure 12. On−Resistance Variation with Drain Current and Gate Voltage

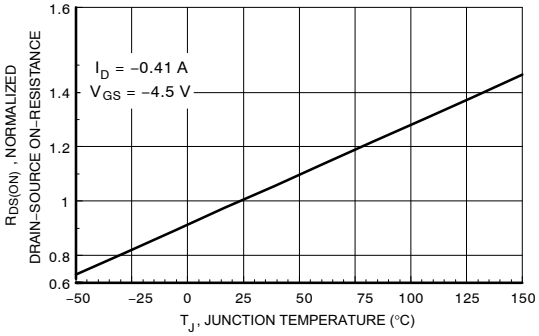


Figure 13. On−Resistance Variation with Temperature

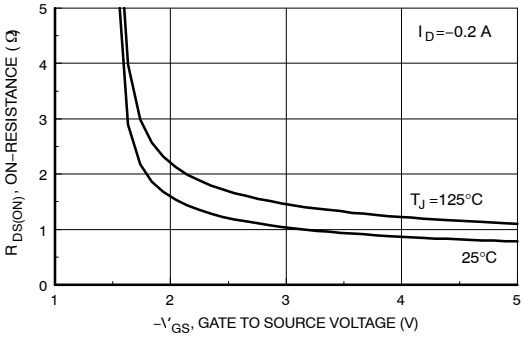


Figure 14. On−Resistance Variation with Gate−to−Source Voltage

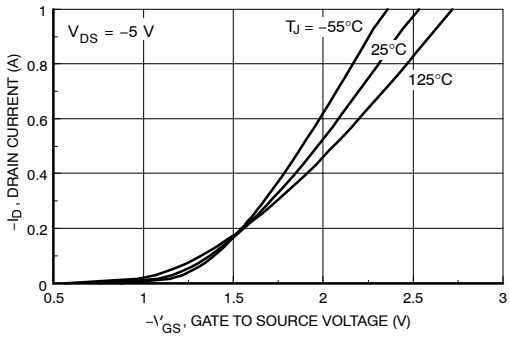


Figure 15. Transfer Characteristics

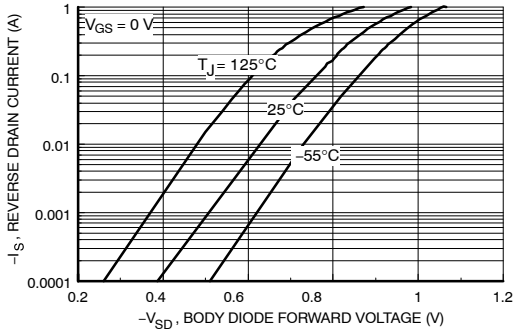


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL PERFORMANCE CHARACTERISTICS: P−CHANNEL (CONTINUED)

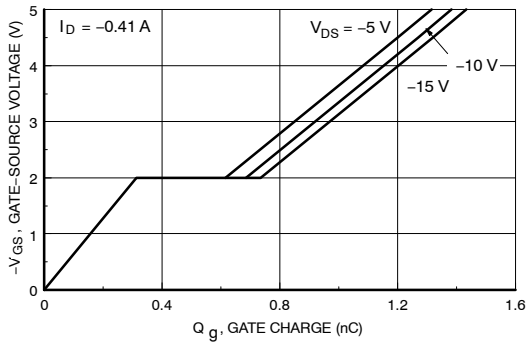


Figure 17. Gate Charge Characteristics

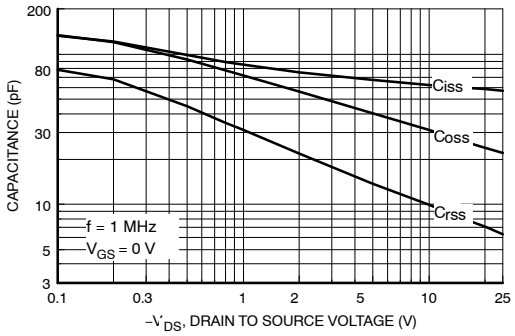


Figure 18. Capacitance Characteristics

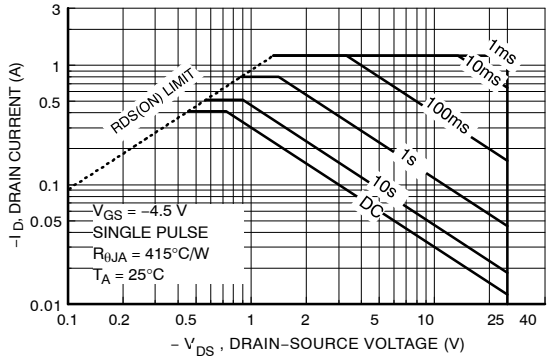


Figure 19. Maximum Safe Operating Area

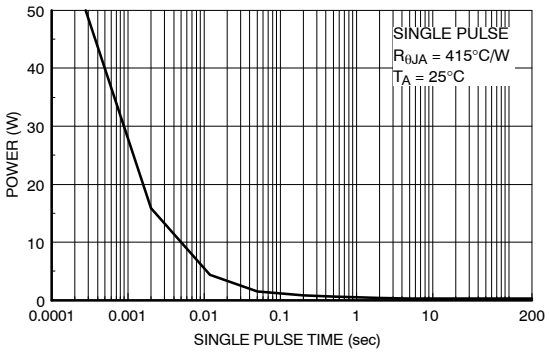


Figure 20. Single Pulse Maximum Power Dissipation

TYPICAL PERFORMANCE CHARACTERISTICS: N & P−CHANNEL

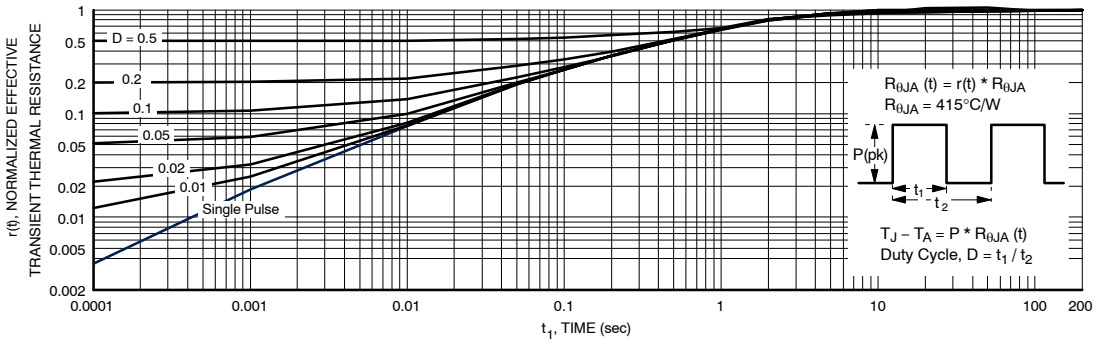
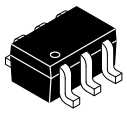


Figure 21. Transient Thermal Response Curve

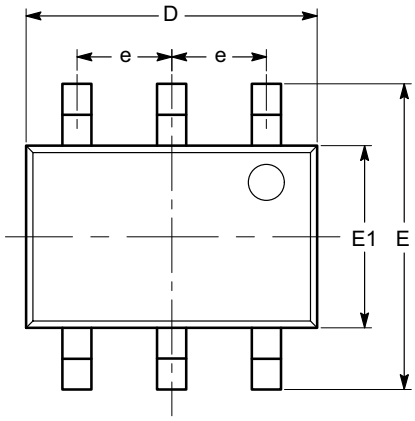
Thermal characterization performed using the conditions described in Note 1.
Transient thermal response will change depending on the circuit board design.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



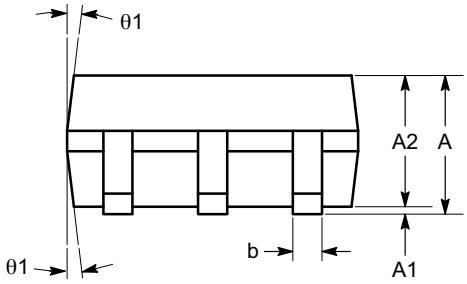
SC−88 (SC−70 6 Lead), 1.25x2
CASE 419AD
ISSUE A

DATE 07 JUL 2010

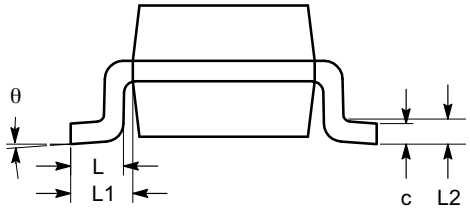


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	0.80		1.10
A1	0.00		0.10
A2	0.80		1.00
b	0.15		0.30
c	0.10		0.18
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
e		0.65 BSC	
L	0.26	0.36	0.46
L1		0.42 REF	
L2		0.15 BSC	
θ	0°		8°
θ1	4°		10°



SIDE VIEW



END VIEW

Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-203.

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DESCRIPTION:	SC−88 (SC−70 6 LEAD), 1.25X2	PAGE 1 OF 1

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